unit: mm

2.9±0.2

2.6±0.1

0.55±0.15

4.6±0.2

.4±0.2

1.6+0.2

8±0.1

15.0±0.5

3.7±0.2 Ē

# 2SK3049

## Silicon N-Channel Power F-MOS FET



- Avalanche energy capacity guaranteed • High-speed switching
- Low ON-resistance
- No secondary breakdown

### Applications

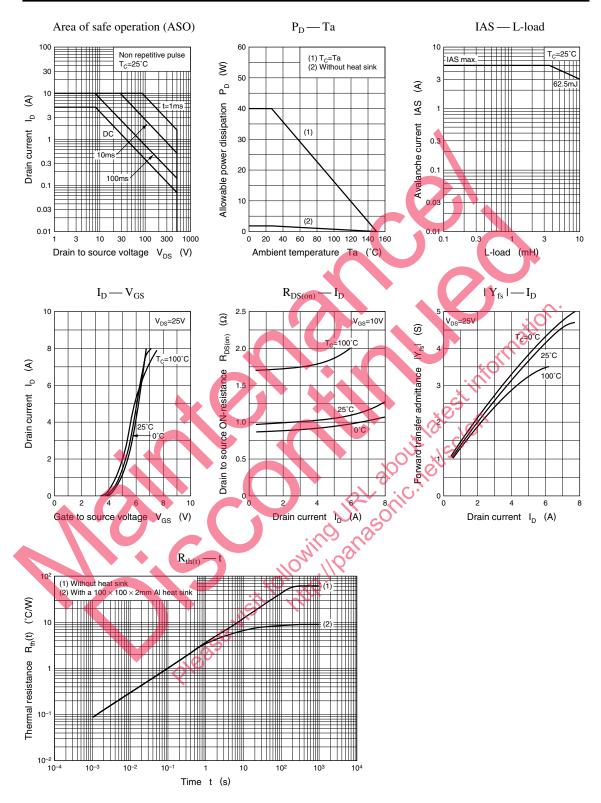
- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

#### Absolute Maximum Ratings ( $T_c = 25^{\circ}C$ )

			<u> </u>				ΨΨ <sup>4</sup> 2.5	4±0.30
Parame	eter	Symbol	Ratings	Unit				8±0.50
Drain to Source brea	akdown voltage	V <sub>DSS</sub>	600	V			123	d
te to Source vo	ltage	V <sub>GSS</sub>	±30	V		Ľ		<u> </u>
•	DC	I <sub>D</sub>	±5	A				ТС
n current	Pulse	I <sub>DP</sub>	±10	A	_		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	~
anche energy	capacity	EAS*	62.5	mJ			0, 16	
able power	$T_C = 25^{\circ}C$	D	40	W		J.		
pation	$Ta = 25^{\circ}C$	P <sub>D</sub>	2	w		°,	2 the	
annel temperat	ure	T <sub>ch</sub>	150	°C	0	$\sim$		
age temperatu	ire	T <sub>stg</sub>	-55 to +150	°C	$\overline{\mathcal{S}}$			
				·	<u> </u>			

#### Electrical Characteristics ( $T_c = 25^{\circ}C$ )

Storage temperature	1 stg	05101150	$\mathcal{L}$			
* L = 5mH, $I_L$ = 5A, 1 pulse		25°C) wing anas	)*			
Electrical Characteristi	CS (T <sub>C</sub> =	25°C)				
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I <sub>DSS</sub>	$V_{\rm DS} = 480 V, V_{\rm GS} = 0$			100	μΑ
Gate to Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30V, V_{DS} = 0$			±1	μΑ
Drain to Source breakdown voltage	V <sub>DSS</sub>	$I_D = 1$ mA, $V_{GS} = 0$	600			V
Gate threshold voltage	V <sub>th</sub>	$V_{DS} = 25V, I_D = 1mA$	2		5	v
Drain to Source ON-resistance	R <sub>DS(on)</sub>	$V_{GS} = 10V, I_D = 3A$		0.85	1.5	Ω
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 25V, I_D = 3A$	1.7	3.4		S
Diode forward voltage	V <sub>DSF</sub>	$I_{DR} = 5A, V_{GS} = 0$			-1.6	v
Input capacitance (Common Source)	C <sub>iss</sub>			1200		pF
Output capacitance (Common Source)	C <sub>oss</sub>	$V_{DS} = 20V, V_{GS} = 0, f = 1MHz$		140		pF
Reverse transfer capacitance (Common Source)	C <sub>rss</sub>			40		pF
Turn-on time (delay time)	t <sub>d(on)</sub>			20		ns
Rise time	t <sub>r</sub>	$V_{DD} = 200V, I_D = 3A$		30		ns
Turn-off time (delay time)	t <sub>d(off)</sub>	$V_{GS} = 10V, R_L = 66.6\Omega$		150		ns
Fall time	t <sub>f</sub>			50		ns



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